



650V Super-Junction Power MOSFET

DESCRIPTION

650V super-junction Power MOSFET

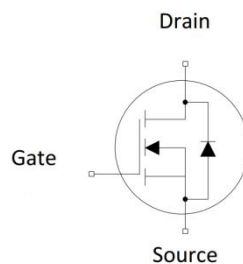
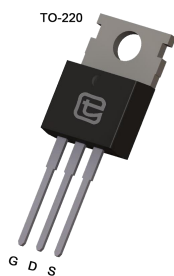
Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The SJ MOSFET is a price-performance optimized product enabling to target cost sensitive applications in Consumer and Lighting markets, also fits the industrial grade applications, like AC-DC SMPS requirements for PFC, AC/DC power conversion, designed by Wuxi Unigroup Microelectronics Company.

FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant
- Industrial grade application

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information

Device	Package	Marking
TPP65R120M	TO-220	65R120M

Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.12	Ω
I_D	30	A
$Q_{g,typ}$	57	nC
I_{DM}	90	A



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	650	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	30
		$T_C = 100^\circ\text{C}$	18
Pulsed Drain Current (note1)	I_{DM}	90	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	636	mJ
Repetitive Avalanche Energy (note2)	E_{AR}	0.96	mJ
Avalanche Current	I_{AR}	5.2	A
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 480\text{V}$	dv/dt	50	V/ns
Power Dissipation	P_D	219	W
Continuous Body Diode Current	I_S	26	A
Pulsed Diode Forward Current (note1)	I_{SM}	90	
Reverse diode dv/dt (note3)	dv/dt	15	V/ns
Maximum diode commutation speed (note3)	di_f/dt	500	A/us
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.57	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	--	4.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 15A$	--	0.105	0.12	Ω
Gate resistance	R_G	$f = 1.0\text{MHz}$ open drain	--	1.5	--	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	2393	--	μF
Output Capacitance	C_{oss}		--	90	--	
Reverse Transfer Capacitance	C_{rss}		--	4	--	
Total Gate Charge	Q_g	$V_{DD} = 520V, I_D = 30A,$ $V_{GS} = 10V$	--	57	--	nC
Gate-Source Charge	Q_{gs}		--	13	--	
Gate-Drain Charge	Q_{gd}		--	21	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 30A,$ $R_G = 25\Omega$	--	24	--	ns
Turn-on Rise Time	t_r		--	40	--	
Turn-off Delay Time	$t_{d(off)}$		--	191	--	
Turn-off Fall Time	t_f		--	73	--	
Drain-Source Body Diode Characteristics						
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 15A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu\text{s}$	--	486	--	ns
Reverse Recovery Charge	Q_{rr}		--	7.4	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	30.6	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 5.2A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical R_G



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

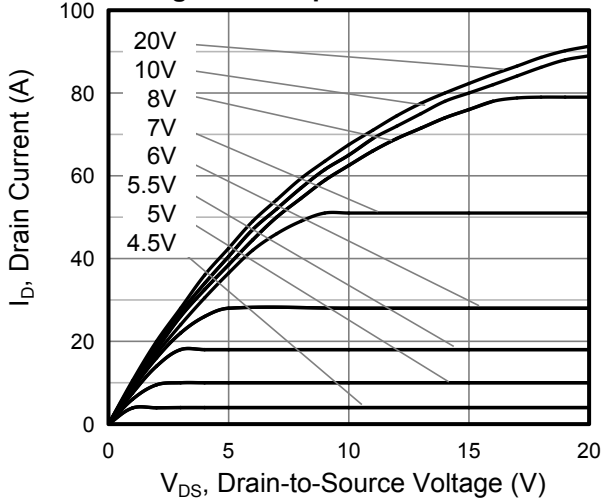


Figure 2. Transfer Characteristics

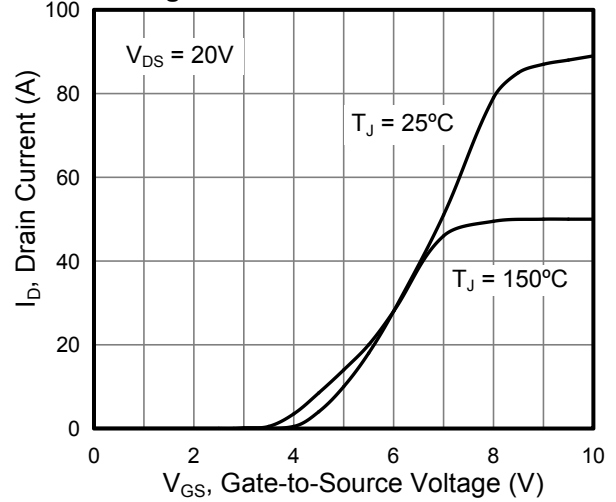


Figure 3. On-Resistance vs. Drain Current

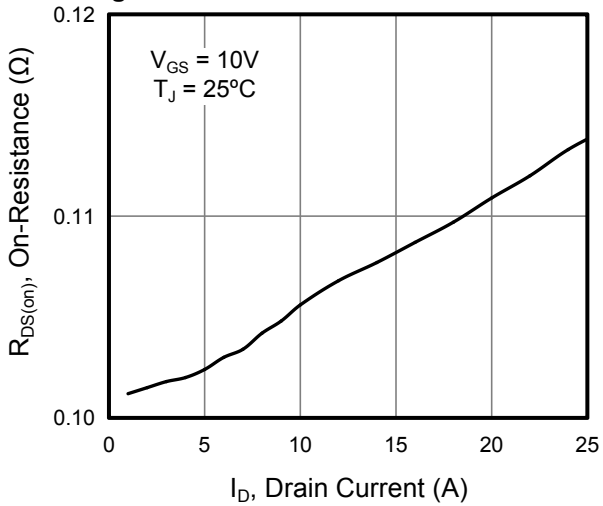


Figure 4. Capacitance

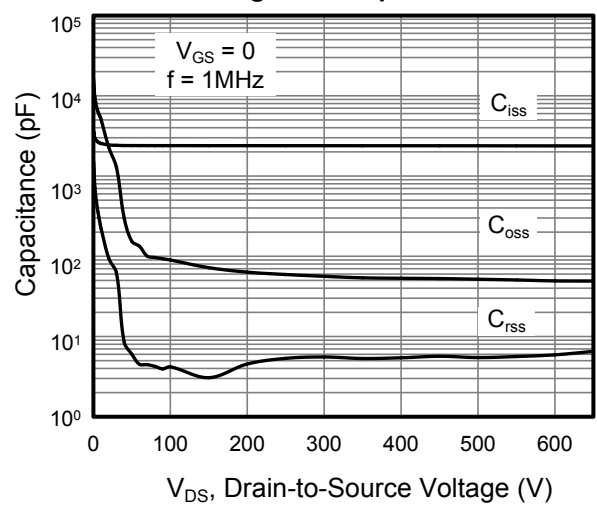


Figure 5. Gate Charge

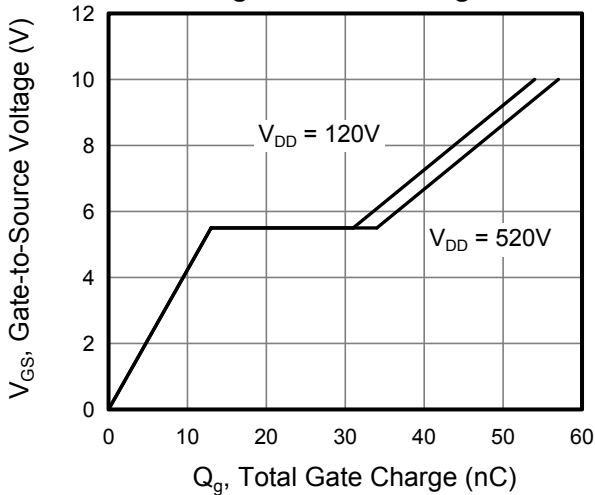
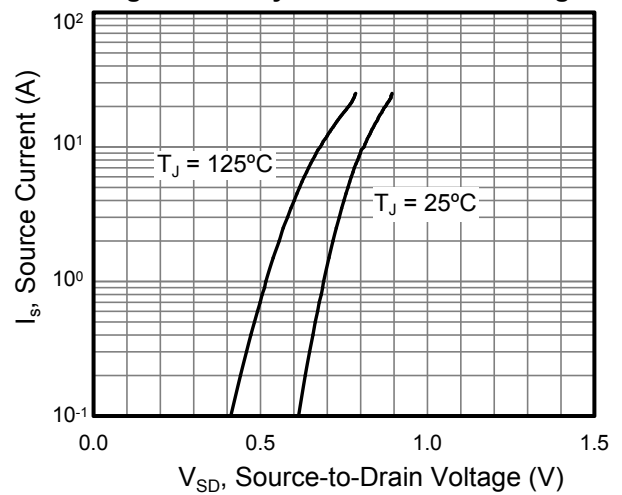


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

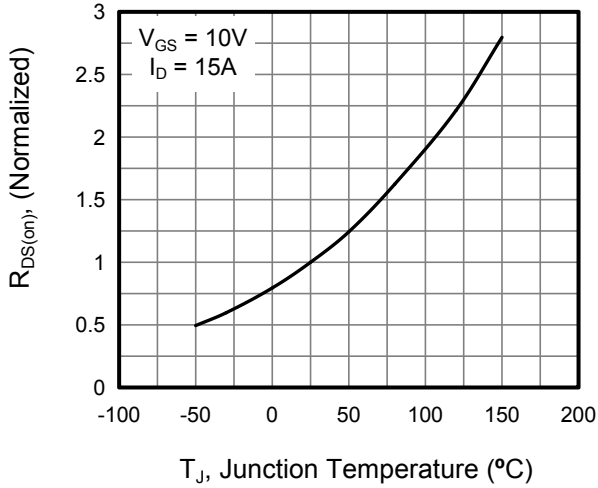


Figure 8. Breakdown voltage vs. Junction Temperature

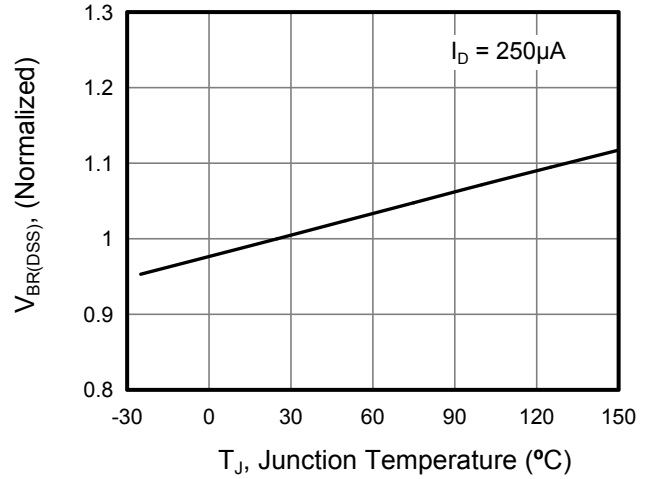


Figure 9. Transient Thermal Impedance TO-220

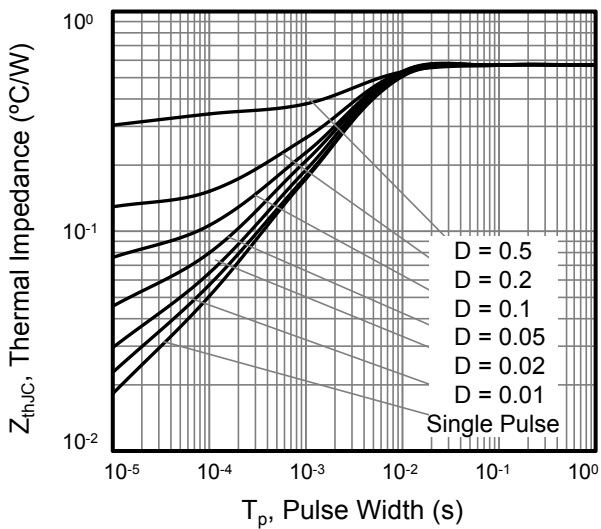


Figure 10. Safe operation area for TO-220

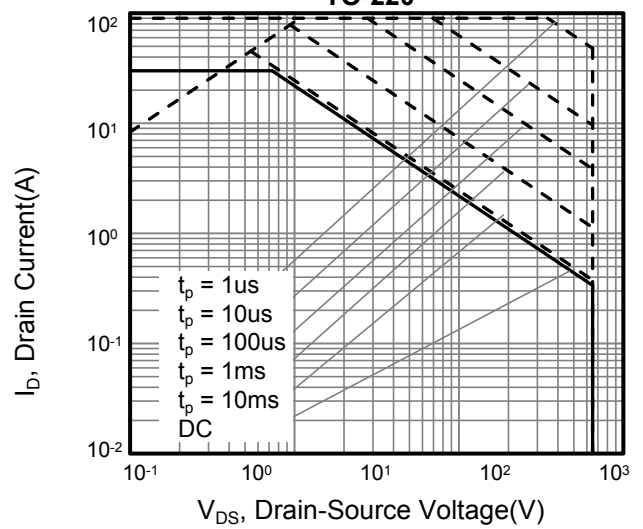




Figure A: Gate Charge Test Circuit and Waveform

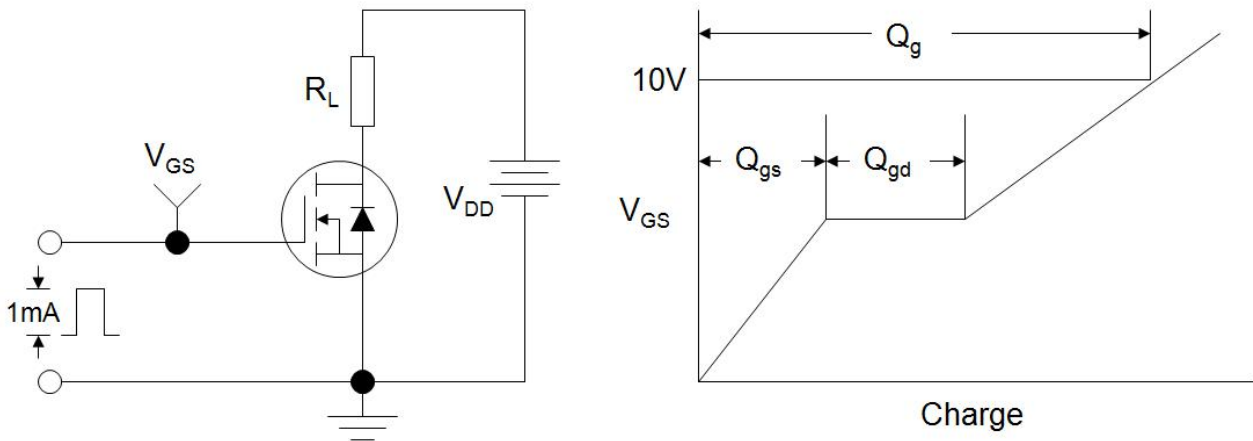


Figure B: Resistive Switching Test Circuit and Waveform

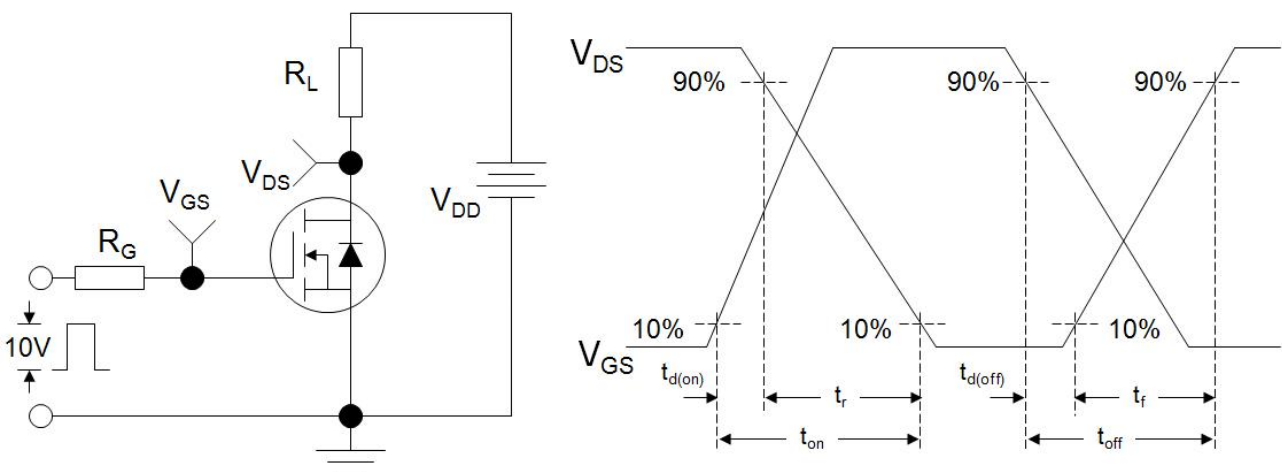
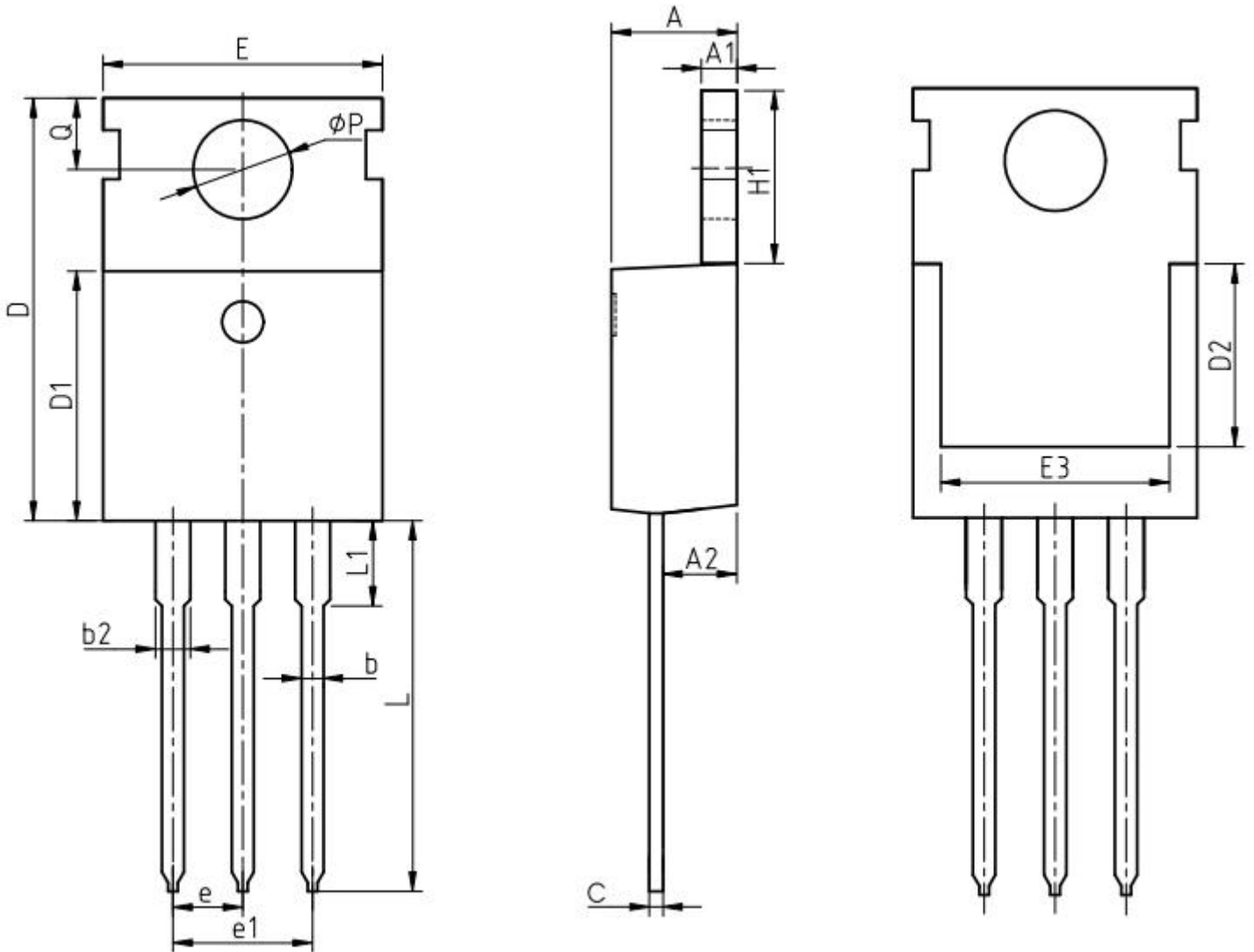


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-220



Unit:mm			
Symbol	Min.	Nom	Max.
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ϕP	3.40	3.60	3.80
Q	2.60	2.80	3.00



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